Abstracts

X and Ku Band High Efficiency Power GaAs FETs

A. Saito, Y. Kojima, K. Suzuki, Y. Kaneko and S. Aihara. "X and Ku Band High Efficiency Power GaAs FETs." 1983 MTT-S International Microwave Symposium Digest 83.1 (1983 [MWSYM]): 265-267.

New structual, high productive power GaAs FETs have been developed, achieving power added efficiency ranging from 30 % to 40 % with 1.5 W power output between 10 to 15.2 GHz on mass production basis. Internally matched devices with two chips have exhibited the supreme performance of 3 W power output with as high as 40 % power added efficiency at 15.2 GHz. These devices have structual features on the 0.5 µm deep recessed gate utilizing photoresist-free gate formation and the sidewall metallization combined with PHS and via hole structure.

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